Supplementary information

Impact of hydrogen dopants incorporation on InGaZnO, ZnO and In_2O_3 thin film transistors

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XPS O1s Spectra for the H-doped InGaZnO, ZnO, In_2O_3 TFTs

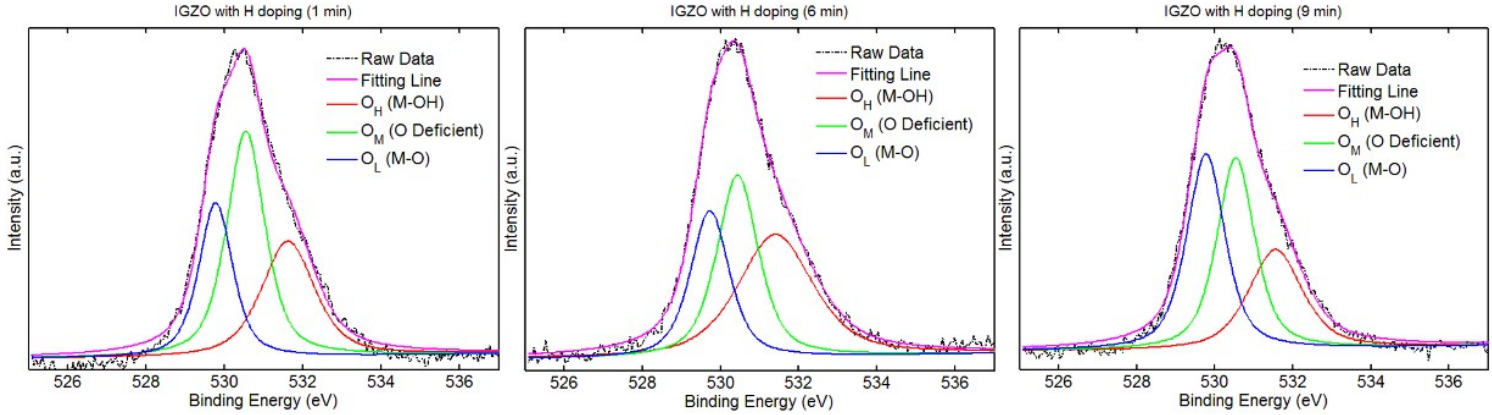

Fig. S1. The XPS O 1s spectra analyzed in the InGaZnO TFTs with H plasma treatment of : (a) 1 minute; (b) 6 minute; (c) 9 minute.

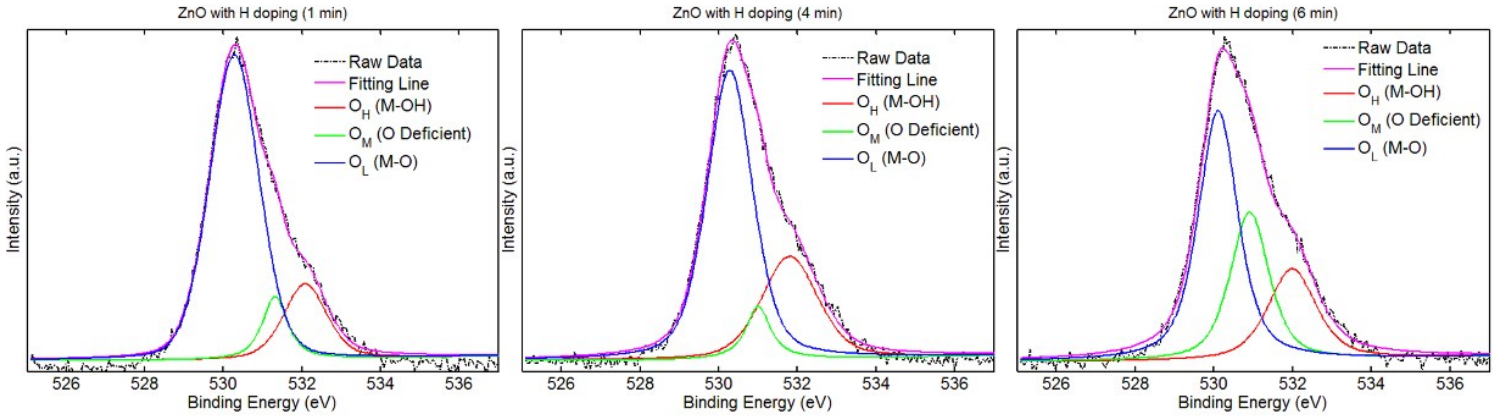

Fig. S2. The XPS O 1s spectra analyzed in the ZnO TFTs with H plasma treatment of : (a) 1 minute; (b) 4 minute; (c) 6 minute.

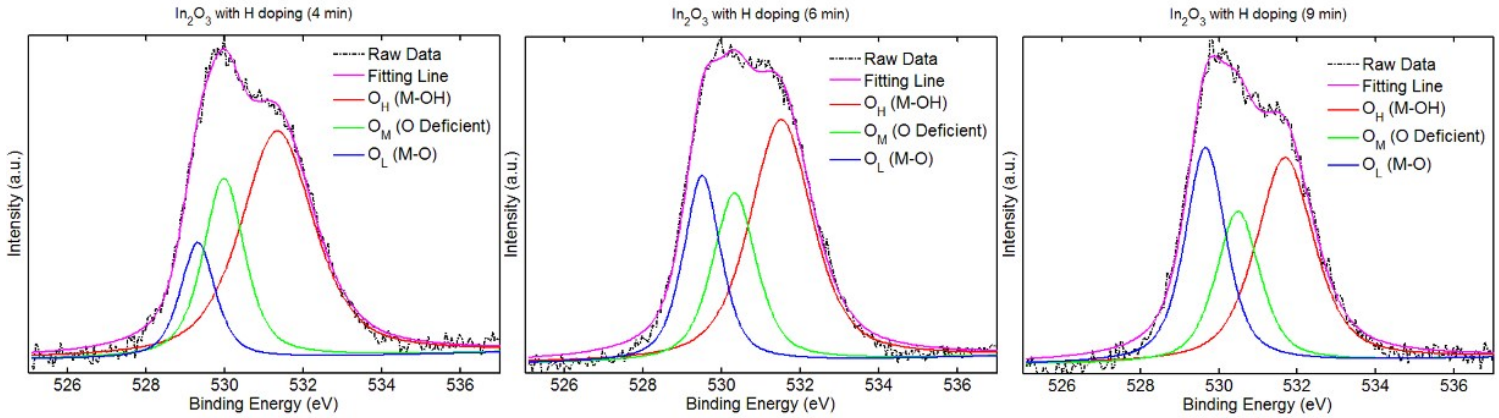

Fig. S3. The XPS O 1s spectra analyzed in the In_2O_3 TFTs with H plasma treatment of : (a) 4 minute; (b) 6 minute; (c) 9 minute.